Publications – Communications relatives au projet P-15-01302

Compound Semiconductors for 3D integration

1. DANOY M., ANGRY P.F., GAVREL J., BRILLARD C., DESPLANQUE L., WANG Y., RUTERANA P., WALLART X.,

Influence of an interfacial AlxIn1-xSb layer on the strain relaxation and surface morphology of thin GaSb layers epitaxially grown on GaAs(001), 26th International Conference on Indium Phosphide and Related Materials, IPRM 2014, Compound Semiconductor Week, CSW 2014, Montpellier, France, may 11-15, 2014 (orale)

2. DANOY M., ANGRY P.F., GAVREL J., BRILLARD C., DESPLANQUE L., WANG Y., RUTERANA P., WALLART X.,

Strain relaxation and surface morphology of thin GaSb layers epitaxially grown on GaAs(001) with interfacial $Al_x In_{1-x}Sb$ layers, 18th International Conference on Molecular Beam Epitaxy, Flagstaff, Arizona, September 7-12 (2014) (poster)

3. DANOY M., ANGRY P.F., GAVRELL J., BRILLARD C., DESPLANQUE L., WANG Y., RUTERANA P., WALLART X.,

Relaxation de contrainte et morphologie de surface de fines couches de GaSb épitaxiées par MBE sur substrat GaAs (001) avec couche interfaciale d'AlInSb, Réunion Plénière Commune du GDR PULSE et du GDR 2974 Nanofils, Toulouse, France, 27-31 octobre, 2014